

## 128-Kbit serial I<sup>2</sup>C bus EEPROM with unique identifier



SO8N (MN) 150 mil width

#### **Product status**

M24128-U

#### Product label



#### **Features**

#### I<sup>2</sup>C interface

- Compatible with the following I<sup>2</sup>C bus modes:
  - 100 kHz (Standard-mode)
  - 400 kHz (Fast-mode)
  - 1 MHz (Fast-mode Plus)

#### Memory

- 128-Kbit (16-Kbyte) of EEPROM
- Page size: 64-byte

#### **Identification page**

512-bit (64-byte) locked in read-only at factory delivery

#### **UID**

• 128-bit (16-byte) unique factory-programmed serial number

#### Supply voltage

Wide voltage range: 1.7 V to 5.5 V

#### **Temperature**

Operating temperature range: -40 °C to +85 °C

#### Performance

- Enhanced ESD and latch-up protection
- ESD protection: 4 kV (HBM)
- More than 4 million write cycles
- More than 200-year data retention

#### **Advanced features**

- Random and sequential read modes
- Hardware write protection of the whole memory array
- Byte and page write within 5 ms

#### **Package**

SO8N (ECOPACK2 compliant)

## **Applications**

### Applications of EEPROM UID include:

- Improved traceability for accessory recognition
- Enhanced repairability



- Promoting sustainability in the consumer and industrial segments, such as:
  - Data centers
  - Logistics
  - Healthcare
  - Personal electronics

DS14837 - Rev 1 page 2/37

# 1 Description

The M24128-U is a 128-Kbit I $^2$ C-compatible EEPROM (electrically erasable programmable memory) organized as 16 K × 8 bits. It can operate with a supply voltage of 1.7 V to 5.5 V, over an ambient temperature range from -40  $^{\circ}$ C to +85  $^{\circ}$ C.

The device offers an additional page, named the identification page (64 bytes). This page stores a 128-bit (16 bytes) unique factory-programmed serial number, which is frozen in read-only mode on delivery from the factory.

The uniqueness of the serial number is ensured across the whole portfolio of serial EEPROMs manufactured by STMicroelectronics, offering a unique identifier.

Figure 1. Logic diagram

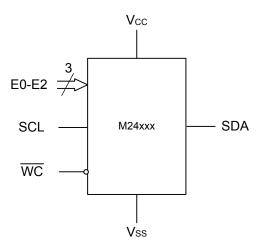
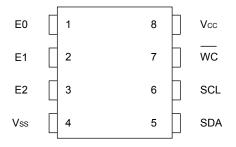


Table 1. Signal names

Signal name	Function	Direction
E2, E1, E0	Chip enable	Input
SDA	Serial data	I/O
SCL	Serial clock	Input
VCC	Supply voltage	-
VSS	Ground	-
WC	Write control	Input

Figure 2. 8-pin package connections, top view



74509V2

DS14837 - Rev 1 page 3/37

JT74693V1



## 2 Signal description

## 2.1 Serial clock (SCL)

SCL is an input. The signal applied on it is used to strobe the data available on SDA(in) and to output the data on SDA(out).

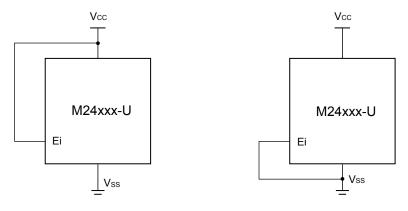
#### 2.2 Serial data (SDA)

SDA is an input/output used to transfer data in or data out of the device. SDA(out) is an open drain output that may be wired-AND with other open drain or open collector signals on the bus. A pull-up resistor must be connected from serial data (SDA) to VCC (Figure 14 and Figure 15 indicate how to calculate the value of the pull-up resistor).

## 2.3 Chip enable (E2, E1, E0)

The input signals E2, E1, and E0 set the value for the three least significant bits (b3, b2, and b1) of the 7-bit device select code (see Table 3). They must be connected to VCC or VSS to establish the device select code, as shown in Figure 3. When they are not connected (left floating), these inputs are read as low (0, 0, 0).

Figure 3. Chip enable inputs connection



## 2.4 Write control (WC)

This input signal is useful for protecting the whole content of the memory from inadvertent write operations. Write operations are:

- Disabled to the whole memory array when write control is driven high.
- Enabled when write control is either driven low or left floating.

When the write control signal is driven high, the device select and address bytes are acknowledged, but data bytes are not acknowledged.

## $V_{SS}$ (ground)

V<sub>SS</sub> is the reference for all signals, including the VCC supply voltage.

## 2.6 Supply voltage (V<sub>CC</sub>)

#### 2.6.1 Operating supply voltage (V<sub>CC</sub>)

Before selecting the memory and issuing instructions to it, a valid and stable  $V_{CC}$  voltage within the specified  $[V_{CC}(min), V_{CC}(max)]$  range must be applied (see Table 7). To secure a stable DC supply voltage, it is recommended to decouple the  $V_{CC}$  line with a suitable capacitor (usually from 10 to 100 nF) close to the VCC/VSS package pins.

This voltage must remain stable and valid until the end of the transmission of the instruction and, for a write instruction, until the completion of the internal write cycle (t<sub>W</sub>).

DS14837 - Rev 1 page 4/37



#### 2.6.2 Power-up conditions

The VCC voltage must rise continuously from 0 V up to the minimum VCC operating voltage (see Table 7).

#### 2.6.3 Device reset

To prevent inadvertent write operations during power-up, a power-on-reset (POR) circuit is included.

At power-up, the device does not respond to any instruction until VCC has reached the internal reset threshold voltage. This threshold is lower than the minimum VCC operating voltage (see Table 7). When VCC passes over the POR threshold, the device is reset and enters the standby power mode; however, the device must not be accessed until VCC reaches a valid and stable DC voltage within the specified  $[V_{CC}(min), V_{CC}(max)]$  range (see Table 7).

Similarly, during power-down, when VCC decreases, the device must not be accessed once VCC drops below VCC(min). When VCC drops below the POR threshold voltage, the device stops responding to any instruction sent to it.

#### 2.6.4 Power-down conditions

During power-down, when VCC decreases, the device must be in the standby power mode (the mode is reached after decoding a stop condition, with no internal write cycle in progress).

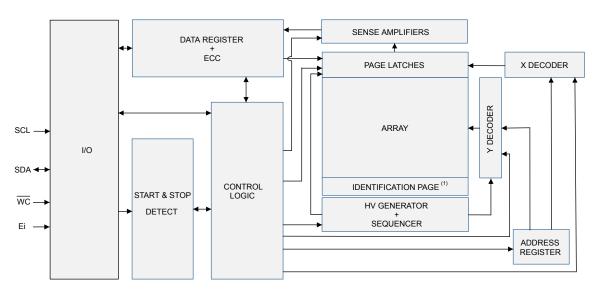
DS14837 - Rev 1 page 5/37



# 3 Memory organization

The memory is organized as shown in the following figure.

Figure 4. Block diagram



1. Identification page with the UID

DS14837 - Rev 1 page 6/37



#### 4 Device features

## 4.1 Identification page

This is an additional 64-byte page, permanently locked in read-only mode. The user can read it by issuing the read identification page instruction. This instruction uses the same protocol and format as the random address read (from the memory array), except for the following differences (refer to Table 3, Table 4, and Table 5):

- Device type identifier = 1011
- MSB address bits from A15 to A8 are Don't care
- LSB address bits from A7 to A6 are Don't care
- LSB address bits from A5 to A0: Define the byte address within the identification page

### 4.2 Unique identifier (UID)

The M24128-U provides an additional feature: a serial number programmed at factory level, and locked in read-only mode within the identification page. This preprogrammed, 16-byte unique ID is a 128-bit serial number.

The 128-bit serial number is unique across the all STMicroelectronics UID-family EEPROM devices.

This UID can be read by issuing the read identification page instruction.

- Device type identifier = 1011
- MSB address bits from A15 to A8 must be equal to 0
- LSB address bits from A7 to A4 must be equal to 0
- LSB address bits from A3 to A0 define the UID byte address within the identification page

The description of the UID is given in the following table.

Table 2. UID address in the identification page

UID address in the identification page (hex)	Description	Value (hex)		
00	Header – STM code	20		
01	Header – Bus protocol	E0		
02	Header - Density	0E		
03	Header – Unused	FF		
04				
05				
06				
07				
08				
09	UID			
0A	Old			
0B				
0C				
0D				
0E				
0F				

DS14837 - Rev 1 page 7/37

DT00792D\_V1

Condition



## 5 Device operation

The device supports the I<sup>2</sup>C protocol. This is summarized in Figure 5. Any device that sends data onto the bus is defined as a transmitter, and any device that reads the data is defined as a receiver. The device that controls the data transfer is known as the bus controller, and the other as the target device. A data transfer can only be initiated by the bus controller, which also provides the serial clock for synchronization. The device is always a target in all communications.

SCL **SDA** SDA-► SDA-► STOP START Input Change Condition Condition SCL MSB **ACK SDA START** Condition SCL MSB **ACK SDA** STOP

Figure 5. I<sup>2</sup>C bus protocol

## 5.1 Start condition

The start condition is identified by a falling edge of serial data (SDA) while the serial clock (SCL) is stable in the high state. This condition must precede any data transfer instruction. The device continuously monitors the SDA and SCL for a start condition, except during a write cycle.

#### 5.2 Stop condition

The stop condition is identified by a rising edge of serial data (SDA) while the serial clock (SCL) is stable in the high state. This condition terminates the communication between the device and the bus controller. A read instruction followed by a NO ACK can be followed by a stop condition to force the device into the standby mode. A stop condition at the end of a write instruction triggers the internal write cycle.

DS14837 - Rev 1 page 8/37



#### 5.3 Data input

During data input, the device samples serial data on the rising edge of the serial clock. For proper device operation, the SDA must be stable during the rising edge of the SCL, and the SDA signal must change only when the SCL is driven low.

#### 5.4 Acknowledge bit (ACK)

The acknowledge bit is used to indicate a successful byte transfer. The bus transmitter, whether a bus controller or target device, releases serial data (SDA) after sending eight bits of data. During the ninth clock pulse period, the receiver pulls SDA low to acknowledge the receipt of the eight data bits.

#### 5.5 Device addressing

To start communication between the bus controller and the target device, the bus controller must initiate a start condition. Following this, the bus controller sends the device select code and bytes address as specified in Table 3, Table 4, and Table 5.

If a match occurs on the device select code, the corresponding device gives an acknowledgment on the serial data (SDA) during the interval. If the device does not match the device select code, it deselects itself from the bus, and goes into standby mode.

The eighth bit is the read/write bit  $(R\overline{W})$ , set to 1 for read operations and to 0 for write operations.

Footures	Device type identifier				Chip enable address			R₩
Features	Bit 7 (MSB) <sup>(1)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0 (LSB)
Memory	1	0	1	0	E2	E1	E0	R₩
Identification page	1	0	1	1	E2	E1	E0	R₩
UID	1	0	1	1	E2	E1	E0	R₩

Table 3. Device select code

Table 4. First byte address

Features	Bit 7 (MSB) <sup>(1)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0 (LSB)
Memory	A15 <sup>(2)</sup>	A14 <sup>(2)</sup>	A13	A12	A11	A10	A9	A8
Identification page	X(3)	X	Х	Х	Х	Х	Х	X
UID	0	0	0	0	0	0	0	0

- 1. The most significant bit, b7, is sent first.
- 2. Don't care
- 3. X = Don't care bit.

Table 5. Second byte address

Features	Bit 7 (MSB) <sup>(1)</sup>	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0 (LSB)
Memory	A7	A6	A5	A4	A3	A2	A1	A0
Identification page	X <sup>(2)</sup>	Х	A5	A4	A3	A2	A1	A0
UID	0	0	0	0	А3	A2	A1	A0

- 1. The most significant bit, b7, is sent first.
- 2. X = Don't care bit.

DS14837 - Rev 1 page 9/37

<sup>1.</sup> The most significant bit, b7, is sent first.



## 6 Instructions

## 6.1 Write operations on memory array

Following a start condition, the bus controller sends a device select code with the RW bit reset to 0. The device acknowledges this, as shown in Figure 6, and waits for two address bytes. The device responds to each address byte with an acknowledge bit, and then waits for the data byte.

When the bus controller generates a stop condition immediately after a data byte ACK bit (in the tenth bit time slot), either at the end of a byte write or a page write, the internal write cycle t<sub>W</sub> is triggered. A stop condition at any other time slot does not trigger the internal write cycle.

After the stop condition and the successful completion of an internal write cycle (t<sub>W</sub>), the device internal address counter is automatically incremented to point to the next byte after the last modified byte.

During the internal write cycle, serial data (SDA) is disabled internally, and the device does not respond to any requests.

If the addressed area is write protected with the write control input (WC) driven high, the write instruction is not executed and the accompanying data bytes are not acknowledged, as shown in Figure 7.

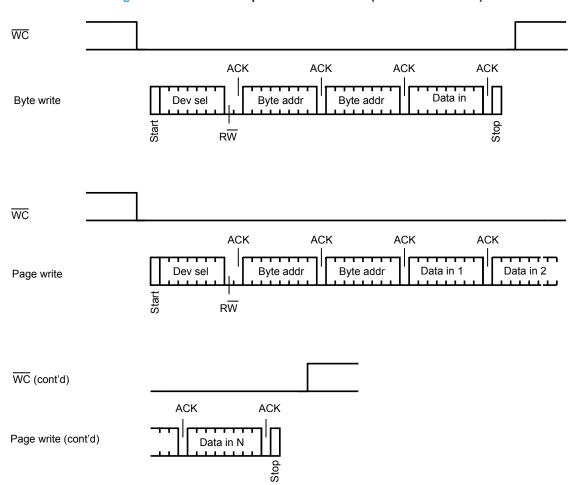
DS14837 - Rev 1 page 10/37

DT01106dV2

#### 6.1.1 Byte write

After the device select code and the address bytes, the bus controller sends one data byte. If the addressed location is write-protected, by write control  $(\overline{WC})$  being driven high, the device replies with NO ACK, and the location is not modified. If, instead, the addressed location is not write-protected, the device replies with ACK. The bus controller terminates the transfer by generating a stop condition, as shown in the following figure.

Figure 6. Write mode sequences with  $\overline{WC} = 0$  (data write enabled)



DS14837 - Rev 1 page 11/37



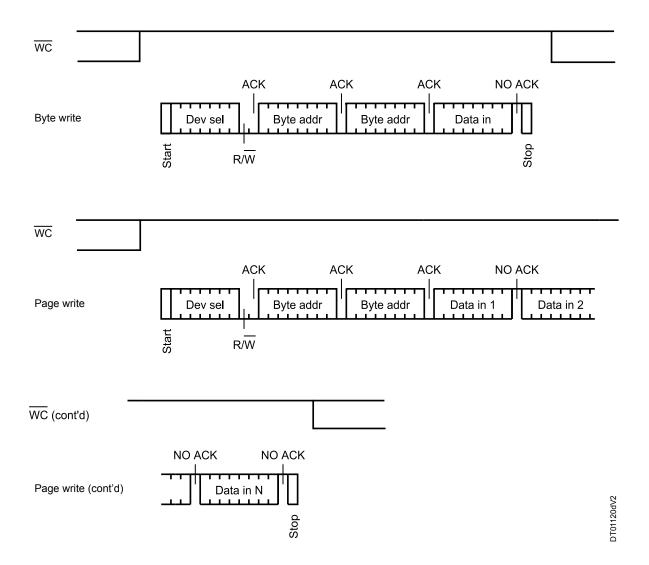
#### 6.1.2 Page write

The page write allows up to 64-byte to be written in a single write cycle, provided that they are all located in the same page. This means the most significant memory address bits from A15 to A6 are the same. If more bytes are sent than fit within the page, a roll-over occurs: the bytes exceeding the page end are written from location 0 on the same page.

The bus controller sends from 1 to 64 bytes of data, each of them is acknowledged by the device if write control (WC) is low. If write control (WC) is high, the contents of the addressed memory location are not modified, and each data byte is followed by a NO ACK, as shown in Figure 7. After each transferred byte, the internal page address counter increments.

The transfer is terminated by the bus controller generating a stop condition.

Figure 7. Write mode sequences with  $\overline{WC}$  = 1 (data write inhibited)



DS14837 - Rev 1 page 12/37



## 6.2 Write operations on the identification page

Write operations on the identification page are not allowed, as this page is delivered locked in read-only.

## 6.3 Error correction code (ECC) and write cycling

The ECC is an internal logic function transparent for the I<sup>2</sup>C communication protocol.

The ECC logic is implemented on each group of four EEPROM bytes. Within a group, if a single bit happens to be erroneous during a read operation, the ECC detects this bit and replaces it with the correct value. The read reliability is therefore much improved.

Even if the ECC function is performed on groups of four bytes, a single byte can be written/cycled independently. In this case, the ECC function also writes/cycles the three other bytes located in the same group (a group of four bytes is located at addresses [4\*N, 4\*N+1, 4\*N+2, 4\*N+3], where N is an integer.)

As a consequence, the maximum cycling budget is defined at group level and the cycling can be distributed over the four bytes of the group: the sum of the cycles seen by byte 0, byte 1, byte 2, and byte 3 of the same group must remain below the maximum value defined in Table 10.

DS14837 - Rev 1 page 13/37



#### 6.4 Minimizing write delays by polling on ACK

During the internal write cycle, the device disconnects itself from the bus, and writes a copy of the data from its internal latches to the memory cells. The maximum write time  $(t_w)$  is shown in the AC characteristics tables in Section 9: DC and AC parameters, but the typical time is shorter. The bus controller can implement a polling sequence to utilize this feature.

The sequence, as shown in Figure 8, is:

- Initial condition: A write cycle is in progress.
- Step 1: The bus controller issues a start condition followed by a device select code (the first byte of the new instruction).
- Step 2: If the device is busy with the internal write cycle, NO ACK is returned and the bus controller goes back to step 1. If the device has terminated the internal write cycle, it responds with an ACK, indicating that the device is ready to receive the second part of the instruction (the first byte of this instruction having been sent during step 1).

Write cycle in progress Start condition Device select with  $R\overline{W} = 0$ ACK NO YES First byte of instruction with  $R\overline{W} = 0$  already decoded by the device Next NO operation is YES addressing the memory Send address and receive ACK Restart Stop NO YES StartCondition Data for the Device select write operation with  $R\overline{W} = 1$ Continue the Continue the

Figure 8. Write cycle polling flowchart using ACK

1. The seven most significant bits of the device select code in a random read (bottom right box in the figure) must match those of the device select code in the write operation (polling instruction in the figure).

write operation

DS14837 - Rev 1 page 14/37

DT01847eV1

random read operation

JT01105dV1



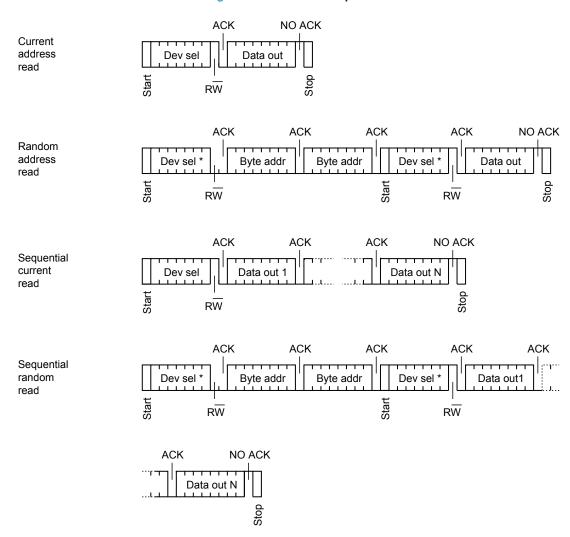
#### 6.5 Read operations on the memory array

Following a start condition the bus controller sends a device select code with the RW bit set to 0. The device acknowledges this and waits for the two-bytes address. The device responds to each address byte with an acknowledge bit. Then, the bus controller sends another start condition, and repeats the device select code, with the RW bit set to 1. The device acknowledges this, and outputs the contents of the data. See in Section 5.5: Device addressing (Table 3, Table 4, and Table 5) how to address the memory array.

After each byte read (data out), the device waits for an acknowledgment (data in) during the ninth bit time. If the bus controller does not acknowledge during this interval, the device terminates the data transfer and switches to its standby mode after a stop condition.

After successfully completing a read operation, the system increments the internal address counter by one to point to the next byte address.

Figure 9. Read mode sequences



Note:

DS14837 - Rev 1 page 15/37

<sup>\*:</sup> The seven most significant bits of the first device select code in a random read must match those of the device select code in the write operation.



#### 6.5.1 Random address read

A dummy write is first performed to load the address into this address counter (as shown in Figure 9. Read mode sequences) without sending a stop condition. Then, the bus controller sends another start condition, and repeats the device select code, with the RW bit set to 1. The device acknowledges this, and outputs the contents of the addressed byte. The bus controller must not acknowledge the byte, and terminates the transfer with a stop condition.

#### 6.5.2 Current address read

For the current address read operation, following a start condition, the bus controller sends only a device select code with the R/W bit set to 1. The device acknowledges this, and outputs the byte addressed by the internal address counter. The counter is then incremented. The bus controller terminates the transfer with a stop condition, as shown in Figure 9. Read mode sequences, without acknowledging the byte.

Note: The address counter value is defined by instructions accessing either the memory or the identification page.

When accessing the identification page, the address counter value is loaded with the identification page byte location, therefore the next current address read in the memory uses this new address counter value. When accessing the memory, it is safer to use the random address read instruction (this instruction loads the address counter with the byte location to read in the memory) instead of the current address read instruction.

#### 6.5.3 Sequential read

This operation can be used after a current address read or a random address read. The bus controller does acknowledge the data byte output, and sends additional clock pulses so that the device continues to output the next byte in sequence. To terminate the stream of bytes, the bus controller must not acknowledge the last byte, and must generate a stop condition, as shown in Figure 9. Read mode sequences.

The output data comes from consecutive addresses, with the internal address counter automatically incremented after each byte output. After the last memory address, the address counter rolls-over, and the device continues to output data from memory address 00h.

DS14837 - Rev 1 page 16/37

DT54535V2



## 6.6 Read operations on identification page

Following a start condition, the bus controller sends a device select code with the  $R\overline{W}$  bit set to 0. The device acknowledges this and waits for the address bytes where the identification page is located. The device responds to each address byte with an acknowledge bit. The bits from A5 to A0 define the byte address within the identification page. Then, the bus controller sends another start condition, and repeats the same device select code but with the  $R\overline{W}$  bit set to 1. The device acknowledges this, and outputs the contents of the identification page. See in Table 3, Table 4, and Table 5 how to address the identification page.

The number of bytes to read in the ID page must not exceed the page boundary (for instance: when reading the identification page from location 10d, the number of bytes should be less than or equal to 54, as the ID page boundary is 64 bytes).

To terminate the stream of data byte, the bus controller must not acknowledge the byte, and must generate a stop condition, as shown in Figure 10.

**ACK ACK** ACK ACK NO ACK Random address Byte addr Dev sel Dev sel Byte addr Data out read Stop Start Start RW RW **ACK ACK ACK ACK ACK** Sequential Dev sel Byte addr Byte addr Dev sel Data out1 random read Start Start RW RW **ACK** NO ACK

Figure 10. Random read on identification page

Note:

\*: The seven most significant bits of the first device select code in a random read must match those of the device select code in the write operation.

Stop

## 6.7 Read lock status on identification page

The lock or unlock status of the identification page can be checked by transmitting a specific truncated command. Following a start condition the bus controller sends a device select code with the  $R\overline{W}$  bit set to 0. The device acknowledges this and waits for the address bytes where the identification page is located. The device responds to each address byte with an acknowledge bit, and then waits for the data byte. See in Table 3, Table 4, and Table 5 how to address the identification page.

The device returns an acknowledge bit after the data byte if the identification page is unlocked (unlock status) as shown in Figure 11, otherwise a NO ACK bit as shown in Figure 12, if the identification page is locked (lock status).

Right after this, it is recommended to transmit to the device a start condition followed by a stop condition, so that:

- Start: the truncated command is not executed because the start condition resets the device internal logic
- Stop: the device is set back into standby mode by the stop condition

Data out N

DS14837 - Rev 1 page 17/37

Figure 11. Read lock status (identification page unlocked)

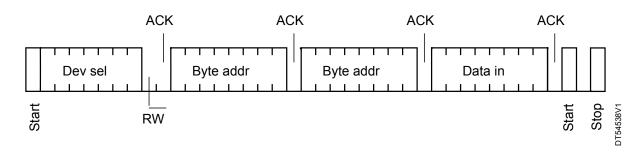
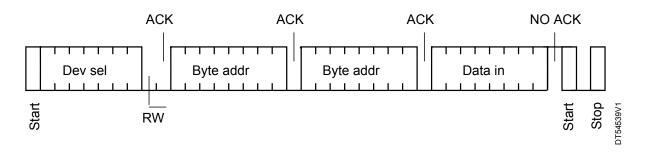


Figure 12. Read lock status (identification page locked)



Note: As the identification page is delivered in read-only mode, the EEPROM consistently behaves as described in Figure 12.

DS14837 - Rev 1 page 18/37



# 7 Initial delivery state

The device is delivered with:

- All the memory array bits are set to 1 (each byte contains FFh).
- The identification page is locked and set with the first 16 bytes containing the value of the UID. The content of the following bytes is FFh.

DS14837 - Rev 1 page 19/37



# 8 Maximum ratings

Stressing the device outside the ratings listed in Table 6 may permanently damage it. These are stress ratings only, and operation of the device at these, or any other conditions outside those indicated in the operating sections of this specification, is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 6. Absolute maximum ratings

Symbol	Parameter	Min.	Max.	Unit
-	Ambient operating temperature	-40	130	°C
T <sub>STG</sub>	Storage temperature	-65	150	°C
T <sub>LEAD</sub>	Lead temperature during soldering	See note (1)		°C
I <sub>OL</sub>	DC output current (SDA = 0)	-	5	mA
V <sub>IO</sub>	Input or output range	-0.50	6.5	V
V <sub>CC</sub>	Supply voltage	-0.50	6.5	V
V <sub>ESD</sub>	Electrostatic pulse (human body model) (2)	-	4000	V

Compliant with JEDEC standard J-STD-020 (for small-body, Sn-Pb or Pb free assembly), the ST ECOPACK 7191395 specification, and the European directive on Restrictions on Hazardous Substances (RoHS directive 2011/65/EU of July 2011).

DS14837 - Rev 1 page 20/37

<sup>2.</sup> Positive and negative pulses applied on different combinations of pin connections, according to AEC-Q100-002 (compliant with ANSI/ESDA/JEDEC JS-001, C1 = 100 pF, R1 = 1500  $\Omega$ ).

DT19774V1



# 9 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device.

**Table 7. Operating conditions** 

Symbol	Parameter	Min.	Max.	Unit
V <sub>CC</sub>	Supply voltage	1.7	5.5	V
T <sub>A</sub>	Ambient operating temperature	-40	85	°C
f <sub>C</sub>	Operating clock frequency	-	1	MHz

Table 8. AC measurement conditions

Symbol	Parameter	Min.	Max.	Unit
C <sub>bus</sub>	Load capacitance	-	100	pF
-	SCL input rise/fall time, SDA input fall time	-	50	ns
-	Input levels	0.2 V <sub>CC</sub> t	o 0.8 V <sub>CC</sub>	V
-	Input and output timing reference levels	0.3 V <sub>CC</sub> t	o 0.7 V <sub>CC</sub>	V

Figure 13. AC measurement I/O waveform

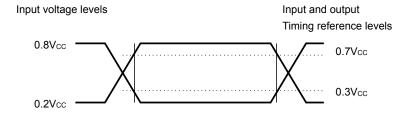


Table 9. Input parameters

Symbol	Parameter	Test condition	Min.	Max.	Unit
C <sub>IN</sub> (1)	Input capacitance (SDA)	-	-	8	pF
C <sub>IN</sub> (1)	Input capacitance (other pins)	-	-	6	pF
Z <sub>L</sub> (2)		V <sub>IN</sub> < 0.3 V <sub>CC</sub>	50	-	1.0
Z <sub>H</sub> <sup>(2)</sup>	Input impedance (E2, E1, E0, WC) <sup>(3)</sup>	V <sub>IN</sub> > 0.7 V <sub>CC</sub>	500	-	kΩ

- 1. Specified by design Not tested in production.
- 2. Evaluated by characterization Not tested in production.
- 3. Input impedance when the memory is selected (after a start condition).

DS14837 - Rev 1 page 21/37



Table 10. Cv	cling performanc	e by aroup:	s of four bytes
--------------	------------------	-------------	-----------------

Symbol	Parameter	Test condition	Max.	Unit
Ncycle	Write cycle endurance <sup>(1)</sup>	$T_A \le 25$ °C, $V_{CC}(min) < V_{CC} < V_{CC}(max)$	4 000 000	Write evelop(2)
		$T_A$ = 85 °C, $V_{CC}$ (min) < $V_{CC}$ < $V_{CC}$ (max)	1 200 000	Write cycles <sup>(2)</sup>

<sup>1.</sup> The write cycle endurance is defined by characterization and qualification. The write cycle endurance is defined for group of four bytes located at addresses [4\*N, 4\*N+1, 4\*N+2, 4\*N+3] where N is an integer.

Table 11. Memory cell data retention

Parameter	Test condition	Min.	Unit
Data retention (1)	T <sub>A</sub> = 55 °C	200	Year

<sup>1.</sup> The data retention behaviour is checked in production, while the data retention limit is extracted from characterization and qualification results.

Table 12. DC characteristics (V<sub>CC</sub> ≥ 1.7 V)

Symbol	Parameter	Parameter Test conditions (in addition to those in Table 7 and Table 8)		Max.	Unit
	Input leakage current	$V_{IN} = V_{SS}$ or $V_{CC}$		± 2	
ILI	(Ei, SCL, SDA)	device in Standby mode	-	ΙZ	μA
I <sub>LO</sub>	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	± 2	μA
	O	$V_{CC} = 1.7 \text{ V, } f_c = 400 \text{ kHz}$	-	0.8	mA
Icc	Supply current (Read)	f <sub>C</sub> = 1 MHz	-	2.5	mA
I <sub>CC0</sub> <sup>(1)</sup>		During t <sub>W</sub> ,			
	Supply current (Write)	V <sub>CC</sub> ≤ 1.8 V	-	2 m	mA
	Otanalla a suranta a surant	Device not selected <sup>(2)</sup> ,		1	
I <sub>CC1</sub>	Standby supply current	$V_{IN} = V_{SS}$ or $V_{CC}$ , $V_{CC} = 1.7 \text{ V}$	-		μA
V <sub>IL</sub>	Input low voltage	V <sub>CC</sub> < 2.5 V	-0.45	0.25 V <sub>CC</sub>	V
VIL	(SCL, SDA, WC, Ei)(3)	VCC \ 2.5 V	-0.45	0.23 V <sub>CC</sub>	V
	Input high voltage	V <sub>CC</sub> < 2.5 V	0.75 V <sub>CC</sub>	6.5	V
V <sub>IH</sub>	(SCL, SDA)	V00 12.0 V	0.70 100	0.0	
V IH	Input high voltage	V <sub>CC</sub> < 2.5 V	0.75 Vcc	V <sub>CC</sub> + 0.6	V
	(WC, Ei) <sup>(4)</sup>		33 *00	100 10.0	
V <sub>OL</sub>	Output low voltage	I <sub>OL</sub> = 1 mA, V <sub>CC</sub> = 1.7 V	-	0.2	V

<sup>1.</sup> Evaluated by characterization - Not tested in production.

DS14837 - Rev 1 page 22/37

<sup>2.</sup> A write cycle is executed when a write instruction is decoded. When using the byte write or the page write, refer also to Section 6.3: Error correction code (ECC) and write cycling.

<sup>2.</sup> The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle t<sub>W</sub> (t<sub>W</sub> is triggered by the correct decoding of a write instruction).

<sup>3.</sup> Ei inputs should be tied to  $V_{SS}$  (see Section 2.3: Chip enable (E2, E1, E0))

<sup>4.</sup> Ei inputs should be tied to V<sub>CC</sub> (see Section 2.3: Chip enable (E2, E1, E0))



Table 13. DC characteristics (V<sub>CC</sub> ≥ 1.8V)

Symbol	Parameter Test conditions (in addition to those in Table 7 and Table 8)		Min.	Max.	Unit
ILI	Input leakage current (Ei, SCL, SDA)	$V_{IN} = V_{SS}$ or $V_{CC}$ , device in standby mode	-	± 2	μA
I <sub>LO</sub>	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$	-	± 2	μA
Icc	County compant (Dood)	$V_{CC} = 1.8 \text{ V}, f_{c} = 400 \text{ kHz}$	-	0.8	Л
	Supply current (Read)	f <sub>c</sub> = 1 MHz	-	2.5	mA
I <sub>CC0</sub> <sup>(1)</sup>	Supply current (Write)	During $t_W$ , $1.8 \text{ V} \leq V_{CC} \leq 2.5 \text{ V}$	-	2	mA
I <sub>CC1</sub>	Standby supply current	Device not selected, (2) $V_{IN} = V_{SS} \text{ or } V_{CC}, V_{CC} = 1.8 \text{ V}$	-	1	μA
V <sub>IL</sub>	Input low voltage (SCL, SDA, WC, Ei)(3)	1.8 V ≤ V <sub>CC</sub> ≤ 2.5 V	-0.45	0.25 V <sub>CC</sub>	V
V <sub>IH</sub>	Input high voltage (SCL, SDA)	1.8 V ≤ V <sub>CC</sub> < 2.5 V	0.75 V <sub>CC</sub>	6.5	V
	Input high voltage (WC, Ei) <sup>(4)</sup>	1.8 V ≤ V <sub>CC</sub> < 2.5 V	0.75 V <sub>CC</sub>	V <sub>CC</sub> + 0.6	V
V <sub>OL</sub>	Output low voltage	I <sub>OL</sub> = 1 mA, V <sub>CC</sub> = 1.8 V	-	0.2	V

- 1. Evaluated by characterization Not tested in production.
- 2. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle t<sub>W</sub> (t<sub>W</sub> is triggered by the correct decoding of a write instruction).
- 3. Ei inputs should be tied to  $V_{SS}$  (see Section 2.3: Chip enable (E2, E1, E0))
- 4. Ei inputs should be tied to  $V_{CC}$  (see Section 2.3: Chip enable (E2, E1, E0))

DS14837 - Rev 1 page 23/37



Table 14. DC characteristics (Vcc ≥ 2.5V)

Symbol	Parameter	Test conditions (in addition to those in Table 7 and Table 8)	Min.	Max.	Unit
ILI	Input leakage current (Ei, SCL, SDA)	V <sub>IN</sub> = V <sub>SS</sub> or V <sub>CC</sub> , device in standby mode		± 2	μA
I <sub>LO</sub>	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: V <sub>SS</sub> or V <sub>CC</sub>	-	± 2	μA
la a	Supply current (Read)	$f_C = 400 \text{ kHz}, 2.5 \text{ V} \le V_{CC} \le 5.5 \text{ V}$	-	2	m 1
I <sub>CC</sub>	Supply current (Reau)	$f_C = 1 \text{ MHz}, 2.5 \text{ V} \le V_{CC} \le 5.5 \text{ V}$	-	2.5	mA
I <sub>CC0</sub> <sup>(1)</sup>	Supply current (Write)	During $t_W$ , 2.5 V $\leq$ V <sub>CC</sub> $\leq$ 5.5 V	-	2.5	mA
laa.	Ctondby gunnly gurrent	Device not selected <sup>(2)</sup> , V <sub>IN</sub> = V <sub>SS</sub> or V <sub>CC</sub> , V <sub>CC</sub> = 2.5 V	-		μA
I <sub>CC1</sub>	Standby supply current	Device not selected <sup>(2)</sup> , V <sub>IN</sub> = V <sub>SS</sub> or V <sub>CC</sub> , V <sub>CC</sub> = 5.5 V	-		μA
V <sub>IL</sub>	Input low voltage (SCL, SDA, WC,Ei)(3)	-	-0.45	0.3 V <sub>CC</sub>	V
V	Input high voltage (SCL, SDA)	-	0.7 V <sub>CC</sub>	6.5	V
V <sub>IH</sub>	Input high voltage (WC, Ei) <sup>(4)</sup>	-	0.7 V <sub>CC</sub>	V <sub>CC</sub> + 0.6	V
V <sub>OL</sub>	Output low voltage	$I_{OL}$ = 2.1 mA, $V_{CC}$ = 2.5 V or $I_{OL}$ = 3 mA, $V_{CC}$ = 5.5 V	-	0.4	V

- 1. Evaluated by characterization Not tested in production.
- 2. The device is not selected after power-up, after a read instruction (after the stop condition), or after the completion of the internal write cycle t<sub>W</sub> (t<sub>W</sub> is triggered by the correct decoding of a write instruction).
- 3. Ei inputs should be tied to  $V_{SS}$  (see Section 2.3: Chip enable (E2, E1, E0)).
- 4. Ei inputs should be tied to V<sub>CC</sub> (see Section 2.3: Chip enable (E2, E1, E0))

DS14837 - Rev 1 page 24/37



Table 15. AC characteristics (Fast-mode)

Symbol	Alt.	Parameter	Min.	Max.	Unit
f <sub>C</sub>	f <sub>SCL</sub>	Clock frequency	-	400	kHz
t <sub>CHCL</sub>	t <sub>HIGH</sub>	Clock pulse width high	600	-	ns
tclch	t <sub>LOW</sub>	Clock pulse width low	1300	-	ns
t <sub>QL1QL2</sub> <sup>(1)</sup>	t <sub>F</sub>	SDA (out) fall time	20(2)	300	ns
t <sub>XH1XH2</sub> <sup>(1)</sup>	t <sub>R</sub>	Input signal rise time	(3)	(3)	ns
t <sub>XL1XL2</sub> <sup>(1)</sup>	t <sub>F</sub>	Input signal fall time	(3)	(3)	ns
t <sub>DXCH</sub>	t <sub>SU:DAT</sub>	Data in set up time	100	-	ns
t <sub>CLDX</sub>	t <sub>HD:DAT</sub>	Data in hold time	0	-	ns
t <sub>CLQX</sub> <sup>(4)</sup>	t <sub>DH</sub>	Data out hold time	50	-	ns
t <sub>CLQV</sub> <sup>(5)</sup>	t <sub>AA</sub>	Clock low to next data valid (access time)	-	900	ns
t <sub>CHDL</sub>	t <sub>SU:STA</sub>	Start condition setup time	600	-	ns
t <sub>DLCL</sub>	t <sub>HD:STA</sub>	Start condition hold time	600	-	ns
t <sub>CHDH</sub>	t <sub>SU:STO</sub>	Stop condition set up time	600	-	ns
t <sub>DHDL</sub>	t <sub>BUF</sub>	Time between Stop condition and next Start condition	1300	-	ns
t <sub>WLDL</sub> <sup>(1)(6)</sup>	t <sub>SU:WC</sub>	WC set up time (before the start condition)	0	-	
t <sub>DHWH</sub> <sup>(1)(7)</sup>	t <sub>HD:WC</sub>	WC hold time (after the stop condition)	1	-	μs
t <sub>W</sub>	t <sub>WR</sub>	Write time	-	5	ms
t <sub>NS</sub> <sup>(1)</sup>	-	Pulse width ignored (input filter on SCL and SDA) - single glitch	-	50	ns

- 1. Evaluated by characterization Not tested in production.
- 2. With  $C_L = 10 pF$ .
- 3. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the  $l^2C$  specification that the input signal rise and fall times be more than 20 ns and less than 300 ns when  $f_C < 400$  kHz.
- To avoid spurious start and stop conditions, a minimum delay is placed between SCL = 1 and the falling or rising edge of SDA.
- t<sub>CLQV</sub> is the time (from the falling edge of SCL) required by the SDA bus line to reach either 0.3 V<sub>CC</sub> or 0.7 V<sub>CC</sub>, assuming that R<sub>bus</sub> × C<sub>bus</sub> time constant is within the values specified in Figure 14.
- 6.  $\overline{WC}$  = 0 set up time condition to enable the execution of a write command.
- 7.  $\overline{WC} = 0$  hold time condition to enable the execution of a write command.

DS14837 - Rev 1 page 25/37



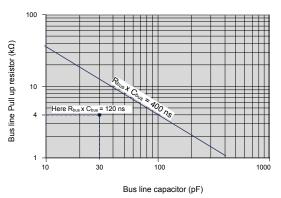
Table 16. AC characteristics (Fast-mode Plus)

Symbol	Alt.	Parameter	Min.	Max.	Unit
f <sub>C</sub>	f <sub>SCL</sub>	Clock frequency	-	1	MHz
t <sub>CHCL</sub>	t <sub>HIGH</sub>	Clock pulse width high	260	-	ns
t <sub>CLCH</sub>	t <sub>LOW</sub>	Clock pulse width low	500	-	ns
t <sub>XH1XH2</sub> (2)	t <sub>R</sub>	Input signal rise time	(1)	(1)	ns
t <sub>XL1XL2</sub> <sup>(2)</sup>	t <sub>F</sub>	Input signal fall time	(1)	(1)	ns
t <sub>QL1QL2</sub> <sup>(2)</sup>	t <sub>F</sub>	SDA (out) fall time	20(3)	120	ns
t <sub>DXCH</sub>	t <sub>SU:DAT</sub>	Data in setup time	50	-	ns
t <sub>CLDX</sub>	t <sub>HD:DAT</sub>	Data in hold time	0	-	ns
t <sub>CLQX</sub> <sup>(4)</sup>	t <sub>DH</sub>	Data out hold time	50	-	ns
t <sub>CLQV</sub> <sup>(5)</sup>	t <sub>AA</sub>	Clock low to next data valid (access time)	-	450	ns
t <sub>CHDL</sub>	t <sub>SU:STA</sub>	Start condition setup time	250	-	ns
t <sub>DLCL</sub>	t <sub>HD:STA</sub>	Start condition hold time	250	-	ns
t <sub>CHDH</sub>	t <sub>SU:STO</sub>	Stop condition setup time	250	-	ns
t <sub>DHDL</sub>	t <sub>BUF</sub>	Time between Stop condition and next Start condition	500	-	ns
t <sub>WLDL</sub> (2)(6)	t <sub>SU:WC</sub>	WC set up time (before the Start condition)	0	-	μs
t <sub>DHWH</sub> <sup>(2)(7)</sup>	t <sub>HD:WC</sub>	WC hold time (after the Stop condition)	1	-	μs
t <sub>W</sub>	t <sub>WR</sub>	Write time	-	5	ms
t <sub>NS</sub> <sup>(2)</sup>	-	Pulse width ignored (input filter on SCL and SDA)	-	50	ns

- 1. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the  $I^2C$  specification that the input signal rise and fall times be less than 120 ns when  $f_C < 1$  MHz.
- 2. Evaluated by characterization Not tested in production.
- 3. With  $C_L = 10 pF$ .
- 4. To avoid spurious start and stop conditions, a minimum delay is placed between SCL = 1 and the falling or rising edge of SDA
- 5.  $t_{CLQV}$  is the time (from the falling edge of SCL) required by the SDA bus line to reach either 0.3  $V_{CC}$  or 0.7  $V_{CC}$ , assuming that the  $R_{bus} \times C_{bus}$  time constant is within the values specified in Figure 15.
- 6.  $\overline{WC}$  = 0 set up time condition to enable the execution of a write command.
- 7.  $\overline{WC} = 0$  hold time condition to enable the execution of a write command.

DS14837 - Rev 1 page 26/37

Figure 14.  $R_{bus}$  value versus bus parasitic capacitance ( $C_{bus}$ ) for an  $I^2C_{bus}$  ( $f_C$  = 400 kHz)



The R<sub>bus</sub> x C<sub>bus</sub> time constant must be below the 400 ns time constant line displayed on the left

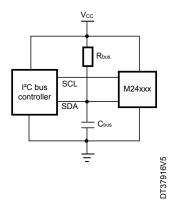
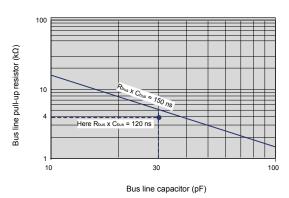
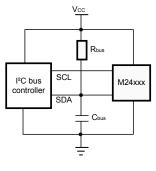


Figure 15.  $R_{bus}$  value versus bus parasitic capacitance ( $C_{bus}$ ) for an  $I^2C$  bus ( $f_C = 1$  MHz)



The R<sub>bus</sub> x C<sub>bus</sub> time constant must be below the 150 ns time constant line displayed on the left

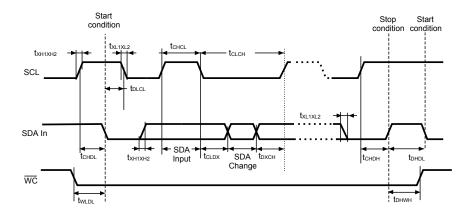


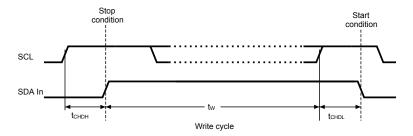
DT19745V8

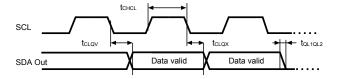
DS14837 - Rev 1 page 27/37



Figure 16. AC waveforms







DT00795iV1



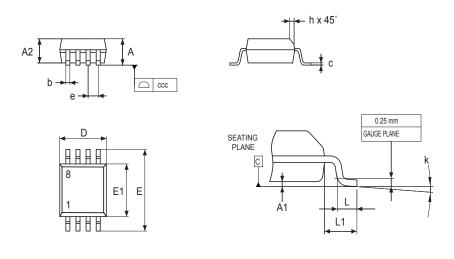
# 10 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

## 10.1 SO8N package information

This SO8N is an 8-lead, 4.9 x 6 mm, plastic small outline, 150 mil body width package.

Figure 17. SO8N - Outline



1. Drawing is not to scale.

DS14837 - Rev 1 page 29/37



Cumbal		millimeters			inches (1)	
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	-	-	1.750	-	-	0.0689
A1	0.100	-	0.250	0.0039	-	0.0098
A2	1.250	-	-	0.0492	-	-
b	0.280	-	0.480	0.0110	-	0.0189
С	0.170	-	0.230	0.0067	-	0.0091
D <sup>(2)</sup>	4.800	4.900	5.000	0.1890	0.1929	0.1969
E	5.800	6.000	6.200	0.2283	0.2362	0.2441
E1 <sup>(3)</sup>	3.800	3.900	4.000	0.1496	0.1535	0.1575
е	-	1.270	-	-	0.0500	-
h	0.250	-	0.500	0.0098	-	0.0197
k	0°	-	8°	0°	-	8°
L	0.400	-	1.270	0.0157	-	0.0500
L1	-	1.040	-	-	0.0409	-
ccc	-	-	0.100	-	-	0.0039

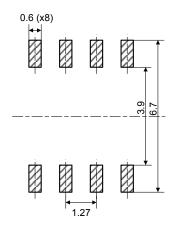
Table 17, SO8N - Mechanical data

- 1. Values in inches are converted from mm and rounded to four decimal digits.
- Dimension D does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side
- 3. Dimension E1 does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25 mm per side.

Note:

The package top may be smaller than the package bottom. Dimensions D and E1 are determinated at the outermost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs, and interleads flash, but including any mismatch between the top and bottom of the plastic body. The measurement side for mold flash, protusions, or gate burrs is the bottom side.

Figure 18. SO8N - Footprint example



07\_S08N\_FP\_V2

1. Dimensions are expressed in millimeters.

DS14837 - Rev 1 page 30/37



## 11 Ordering information

Table 18. Ordering information scheme 128 Example: M24 MN 6 /K **Device type** M24 = I2C serial access EEPROM **Device function** 128 = 128-Kbit (16K x 8 bit) **Device family** U = With UID Operating voltage  $F = V_{CC} = 1.7 \text{ V to } 5.5 \text{ V}$ Package<sup>(1)</sup> MN = SO8N (150 mil width) **Device grade** 6 = Industrial: device tested with standard test flow over -40 to 85 °C Option T = Tape and reel packing Blank = tube packing **Plating technology** P or G = RoHS compliant and halogen-free (ECOPACK2)

/K = Manufacturing technology code

- 1. All packages are ECOPACK2 (RoHS-compliant and free of brominated, chlorinated and antimony-oxide flame retardants).
- 2. The process letter appears on the device package (marking) and on the shipment box. Contact your nearest ST Sales Office for further information.

Note: For a list of available options (memory, package, and so on) or for further information on any aspect of this device, contact your nearest ST sales office.

Note: Parts marked as "ES" or "E" are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

DS14837 - Rev 1 page 31/37



# **Revision history**

Table 19. Document revision history

Date	Revision	Changes
21-Feb-2025	1	Initial release.

DS14837 - Rev 1 page 32/37



# **Contents**

1	Desc	cription	1	3
2	Sign	al desc	cription	4
	2.1	Serial	clock (SCL)	4
	2.2	Serial	data (SDA)	4
	2.3	Chip e	enable (E2, E1, E0)	4
	2.4	Write	control (WC)	4
	2.5	V <sub>SS</sub> (g	ground)	4
	2.6	Supply	y voltage (V <sub>CC</sub> )	4
		2.6.1	Operating supply voltage (V <sub>CC</sub> )	4
		2.6.2	Power-up conditions	5
		2.6.3	Device reset	5
		2.6.4	Power-down conditions	5
3	Mem	ory org	ganization	6
4	Devi	ce feat	ures	7
	4.1	Identif	ication page	7
	4.2	Uniqu	ue identifier (UID)	7
5	Devi	ce ope	ration	8
	5.1	Start c	condition	8
	5.2	Stop c	condition	8
	5.3	Data ir	nput	9
	5.4	Ackno	wledge bit (ACK)	9
	5.5	Device	e addressing	9
6	Instr	uctions	s	10
	6.1	Write	operations on memory array	10
		6.1.1	Byte write	11
		6.1.2	Page write	12
	6.2	Write	operations on the identification page	13
	6.3	Error o	correction code (ECC) and write cycling	13
	6.4	Minimi	izing write delays by polling on ACK	14
	6.5	Read	operations on the memory array	15
		6.5.1	Random address read	
		6.5.2	Current address read	
		6.5.3	Sequential read	
	6.6	Read	operations on identification page	17



	6.7 Read lock status on identification page	
7	Initial delivery state	19
8	Maximum ratings	20
9	DC and AC parameters	21
10	Package information	29
	10.1 SO8N package information	29
11	Ordering information	31
Rev	evision history	32



# **List of tables**

Table 1.	Signal names	. :
Table 2.	UID address in the identification page	
Table 3.	Device select code	
Table 4.	First byte address	
Table 5.	Second byte address	. 9
Table 6.	Absolute maximum ratings	20
Table 7.	Operating conditions	21
Table 8.	AC measurement conditions	21
Table 9.	Input parameters	21
Table 10.	Cycling performance by groups of four bytes	22
Table 11.	Memory cell data retention	22
Table 12.	DC characteristics ( $V_{CC} \ge 1.7 \text{ V}$ )	22
Table 13.	DC characteristics (V <sub>CC</sub> ≥ 1.8V)	23
Table 14.	DC characteristics (Vcc ≥ 2.5V)	
Table 15.	AC characteristics (Fast-mode)	
Table 16.	AC characteristics (Fast-mode Plus)	
Table 17.	SO8N - Mechanical data	
Table 18.	Ordering information scheme	
Table 19.	Document revision history	



# **List of figures**

Figure 1.	Logic diagram	. 3
Figure 2.	8-pin package connections, top view	
Figure 3.	Chip enable inputs connection	
Figure 4.	Block diagram	
Figure 5.	I <sup>2</sup> C bus protocol	. 8
Figure 6.	Write mode sequences with WC = 0 (data write enabled)	11
Figure 7.	Write mode sequences with WC = 1 (data write inhibited)	12
Figure 8.	Write cycle polling flowchart using ACK	14
Figure 9.	Read mode sequences	15
Figure 10.	Random read on identification page	17
Figure 11.	Read lock status (identification page unlocked)	18
Figure 12.	Read lock status (identification page locked)	18
Figure 13.	AC measurement I/O waveform	21
Figure 14.	$R_{bus}$ value versus bus parasitic capacitance ( $C_{bus}$ ) for an $I^2C_{bus}$ ( $I_C = 400 \text{ kHz}$ )	27
Figure 15.	$R_{bus}$ value versus bus parasitic capacitance ( $C_{bus}$ ) for an I <sup>2</sup> C bus ( $f_{C}$ = 1 MHz)	27
Figure 16.	AC waveforms	28
Figure 17.	SO8N - Outline	29
Figure 18.	SO8N - Footprint example	30



#### **IMPORTANT NOTICE - READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to <a href="https://www.st.com/trademarks">www.st.com/trademarks</a>. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2025 STMicroelectronics – All rights reserved

DS14837 - Rev 1 page 37/37